

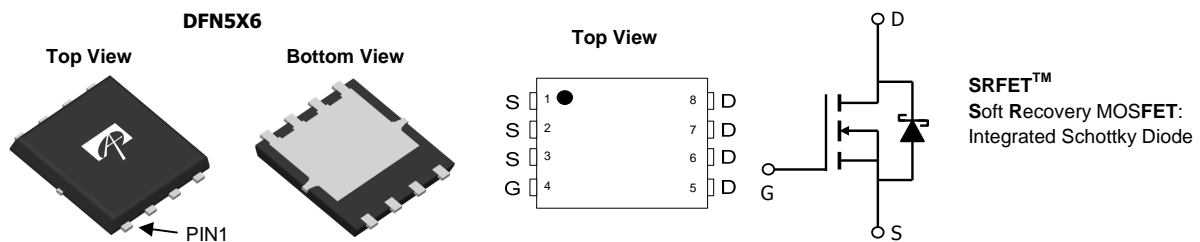
General Description

SRFET™ AON6718 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent $R_{DS(ON)}$ and low gate charge. This device is ideally suited for use as a low side switch in CPU core power conversion.

Product Summary

V_{DS} (V) = 30V
 I_D = 80A ($V_{GS} = 10V$)
 $R_{DS(ON)} < 3.7m\Omega$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 5m\Omega$ ($V_{GS} = 4.5V$)

100% UIS Tested
 100% Rg Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ\text{C}$	80
		$T_C=100^\circ\text{C}$	63
Pulsed Drain Current ^C	I_{DM}	210	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	18
		$T_A=70^\circ\text{C}$	15
Avalanche Current ^C	I_{AR}	40	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	80	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	83
		$T_C=100^\circ\text{C}$	33
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	2.1
		$T_A=70^\circ\text{C}$	1.3
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	14.2	17	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}		Steady-State	42	60
Maximum Junction-to-Case	$R_{\theta JC}$	1.2	1.5	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
B _V DSS	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =125°C		0.025	0.1 20	mA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			0.1	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1.3	1.8	2.2	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	160			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		3.1 4.3	3.7 5.2	mΩ
		V _{GS} =4.5V, I _D =20A		4.1	5	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		87		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.4	0.7	V
I _S	Maximum Body-Diode Continuous Current ^G				40	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz	2975	3719	4463	pF
C _{oss}	Output Capacitance		485	693	900	pF
C _{rss}	Reverse Transfer Capacitance		204	340	476	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.28	0.56	0.84	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A	48	60	72	nC
Q _{g(4.5V)}	Total Gate Charge		20	25	30	nC
Q _{gs}	Gate Source Charge		12	15	18	nC
Q _{gd}	Gate Drain Charge		6	10	14	nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		9.2		ns
t _r	Turn-On Rise Time			10.7		ns
t _{D(off)}	Turn-Off DelayTime			40		ns
t _f	Turn-Off Fall Time			12.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs	10	13	16	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs	21	26.5	32	nC

- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is limited by bond-wires.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

Rev3: Nov-10

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

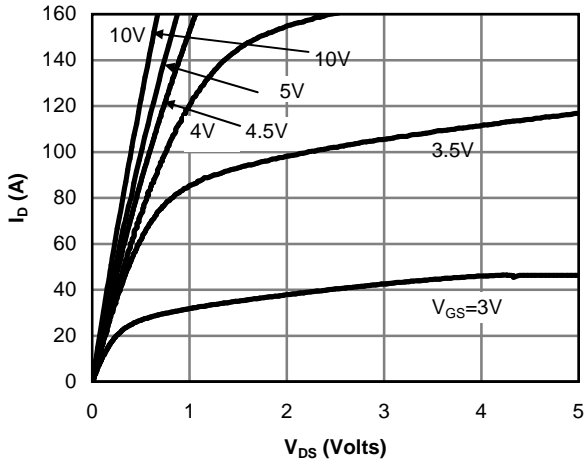


Fig 1: On-Region Characteristics (Note E)

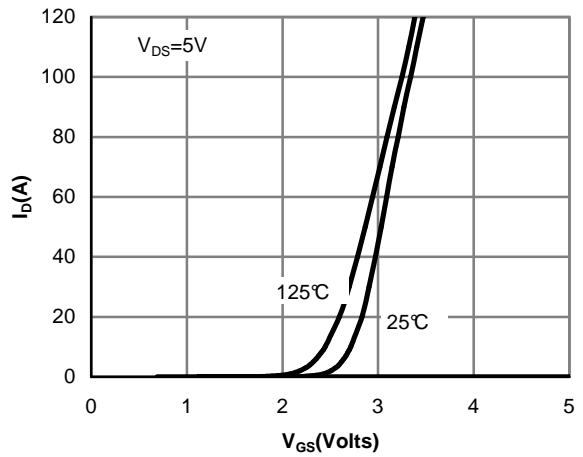


Figure 2: Transfer Characteristics (Note E)

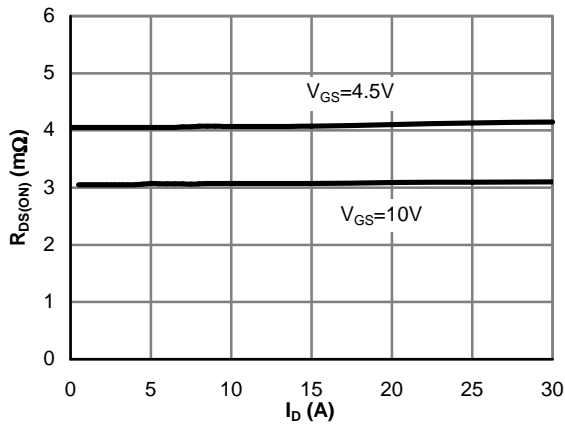


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

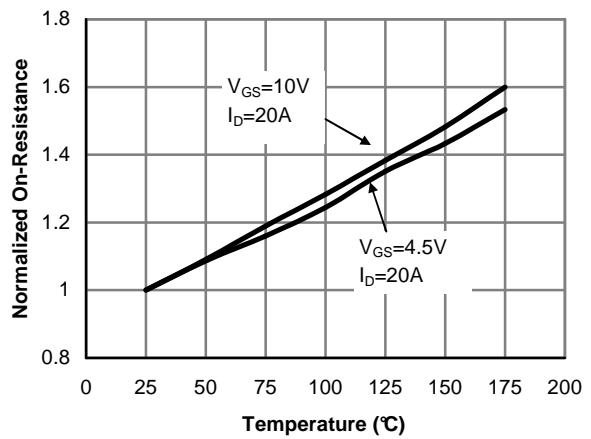


Figure 4: On-Resistance vs. Junction Temperature (Note E)

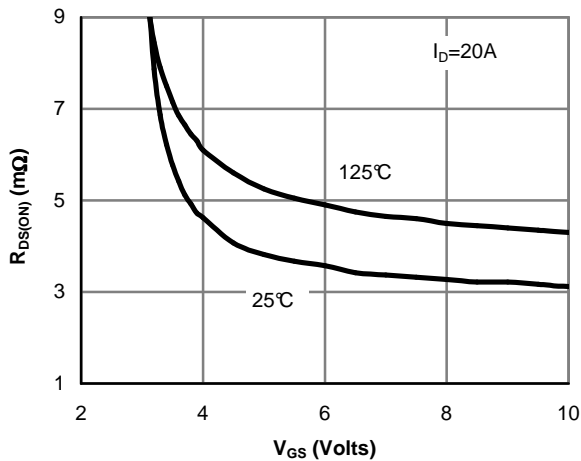


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

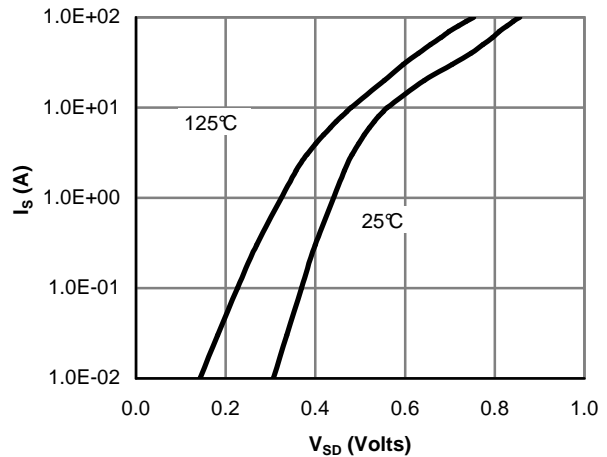


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

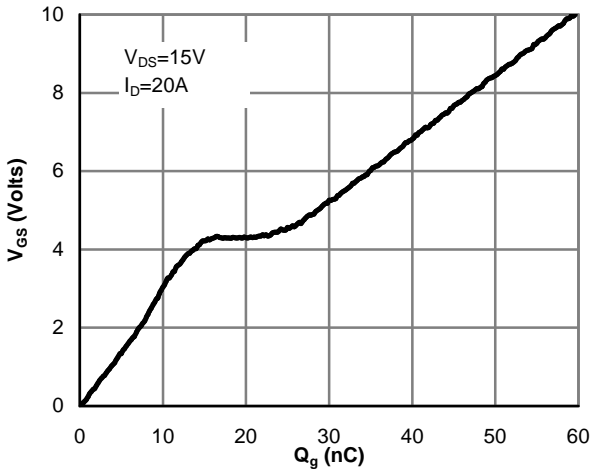


Figure 7: Gate-Charge Characteristics

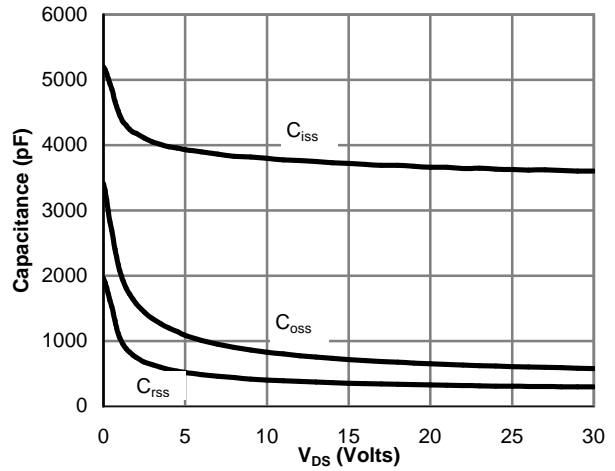


Figure 8: Capacitance Characteristics

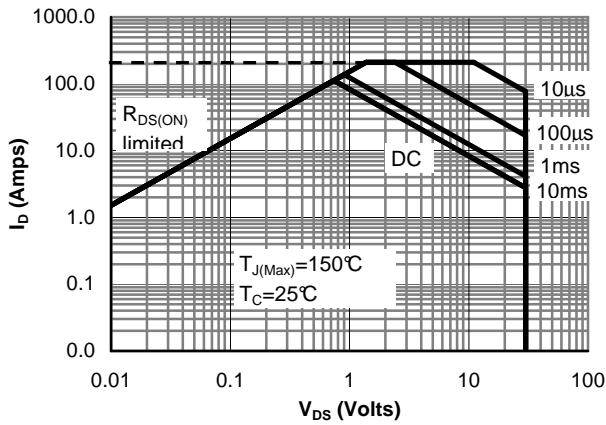


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

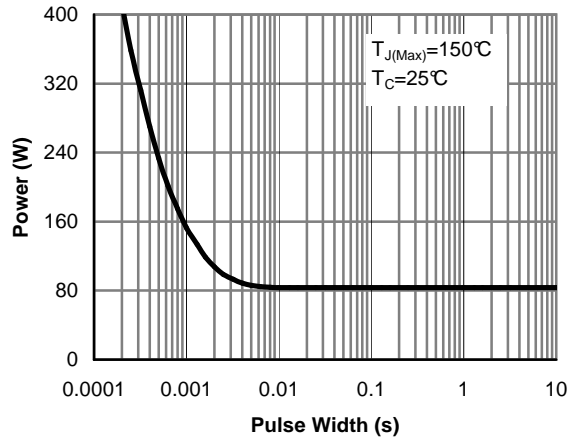


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

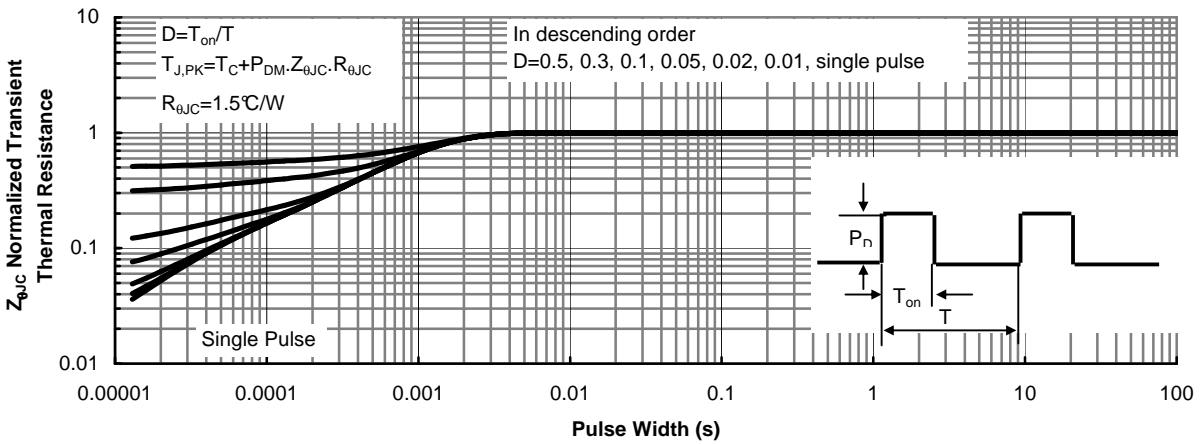


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

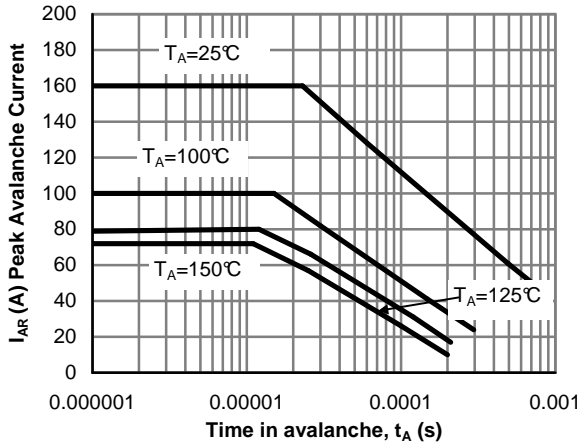


Figure 12: Single Pulse Avalanche capability (Note C)

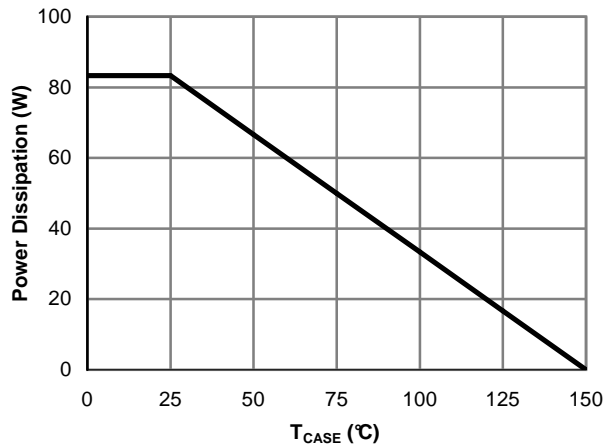


Figure 13: Power De-rating (Note F)

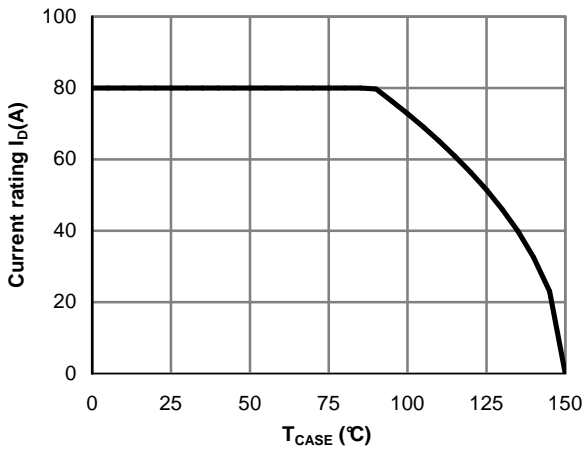


Figure 14: Current De-rating (Note F)

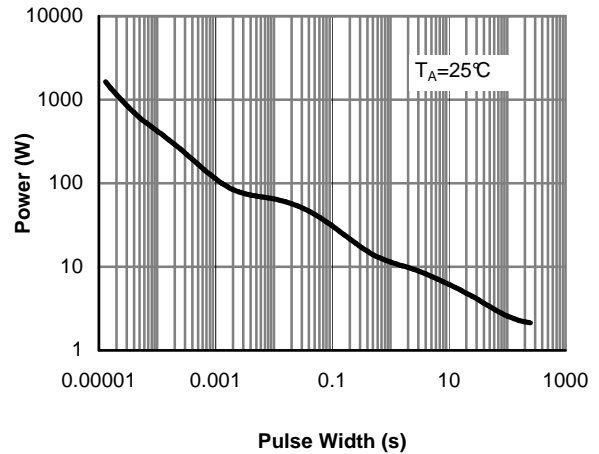


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

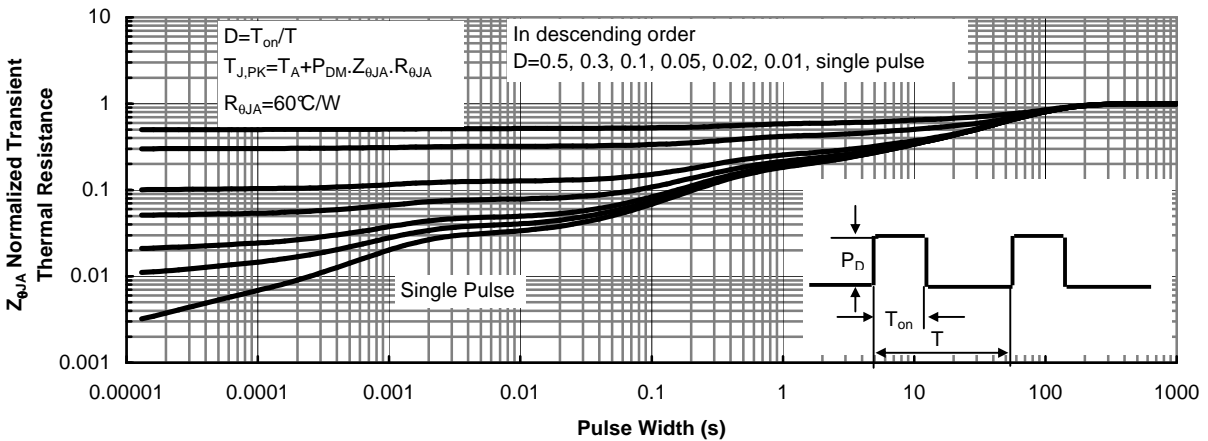


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

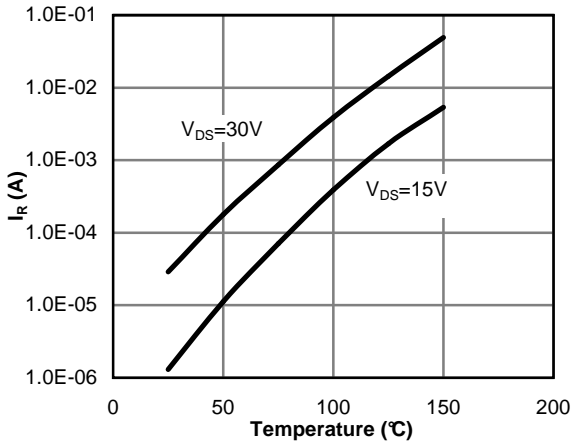


Figure 17: Diode Reverse Leakage Current vs. Junction Temperature

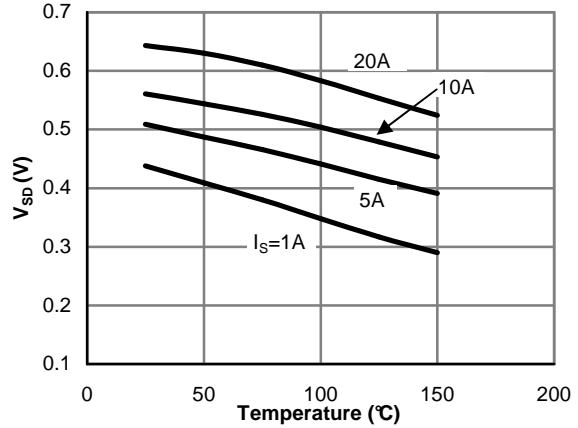


Figure 18: Diode Forward voltage vs. Junction Temperature

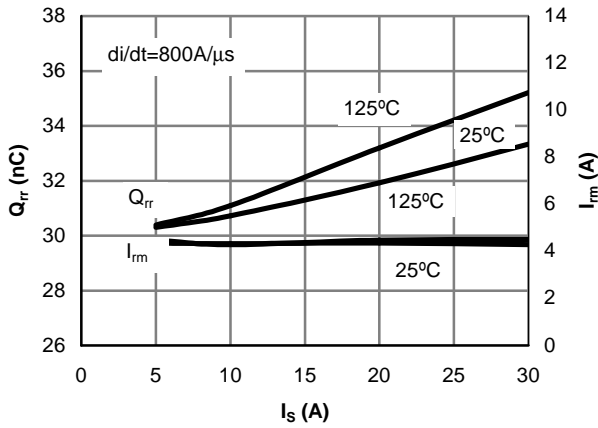


Figure 19: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current

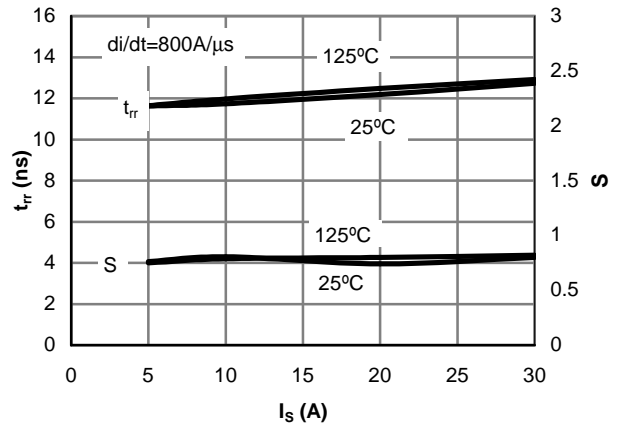


Figure 20: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current

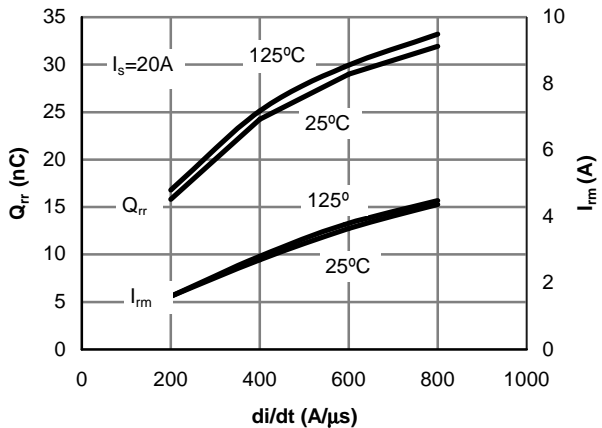


Figure 21: Diode Reverse Recovery Charge and Peak Current vs. di/dt

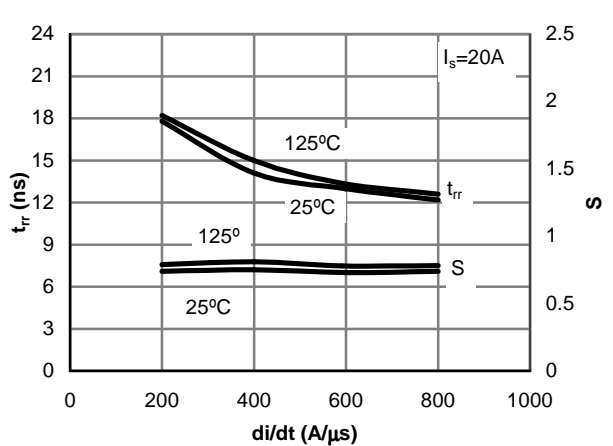
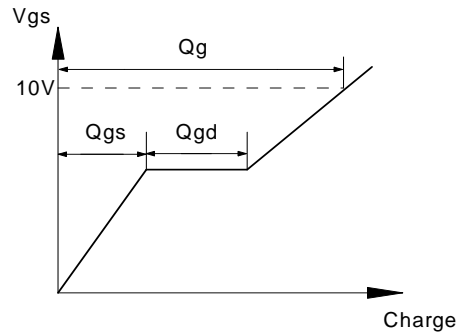
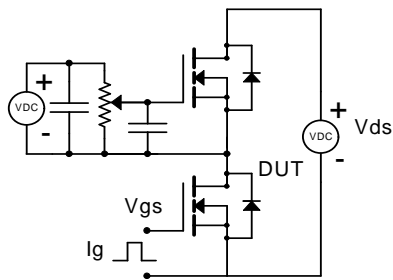
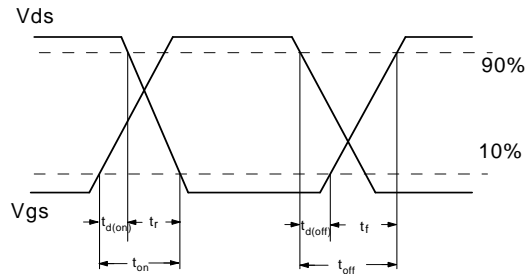
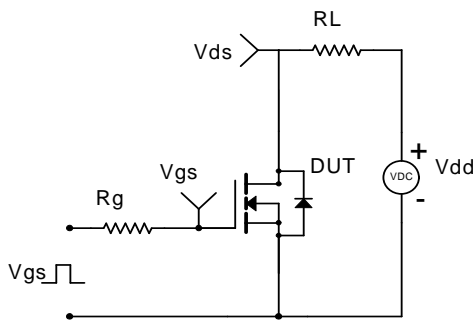


Figure 22: Diode Reverse Recovery Time and Softness Factor vs. di/dt

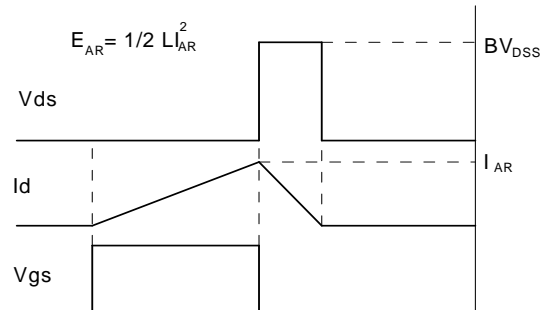
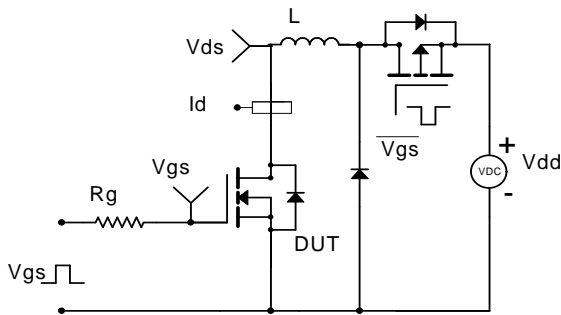
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

